

/ Descriptions

PDFN5×6A 雙 N 溝 1

Dual N-CHANNEL MOSFET in a PDFN5×6A Plastic Package.

/ Features

Dual N-Ch

$V_{DS}(V)=40V$

$I_D=60.2A$

$R_{DS(ON)}<6.5m\Omega(V_{GS}=10V)$

$R_{DS(ON)}<12.5m\Omega(V_{GS}=4.5V)$

1 AEC-Q101 車 用 工 業 產 品

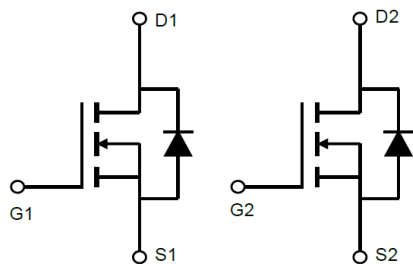
Qualified to AEC-Q101 Standards for High Reliability; HF Product.

/ Applications

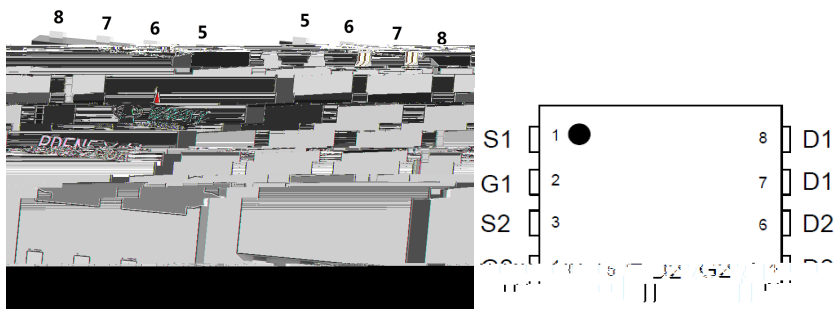
PWM 電 機 驅 動 LED 照 明 電 路 等

PWM Application, Load Switch, Power Management, Dimming LED, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



/ Marking

See Marking Instructions.

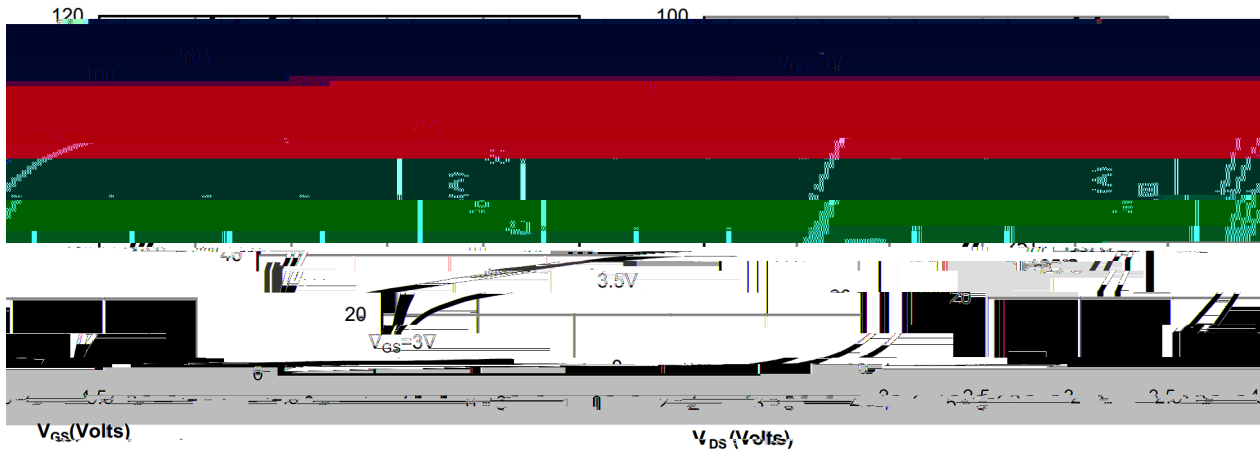
BRCS060N04YMQ

Rev.B Mar.-2023

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	60.2	A
Drain Current - Pulsed	I_{DM}	217	A
Gate-Source Voltage	V_{GS}	± 20	V
Single Pulsed Avalanche Energy	E_{AS}	240.1	mJ
Avalanche Current	I_{AS}	24.5	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	36	W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	trn-On	DeUnit w0T				

/ Electrical Characteristic Curve



Transfer Characteristics

Fig 1: On-Region Characteristics

Figure 2

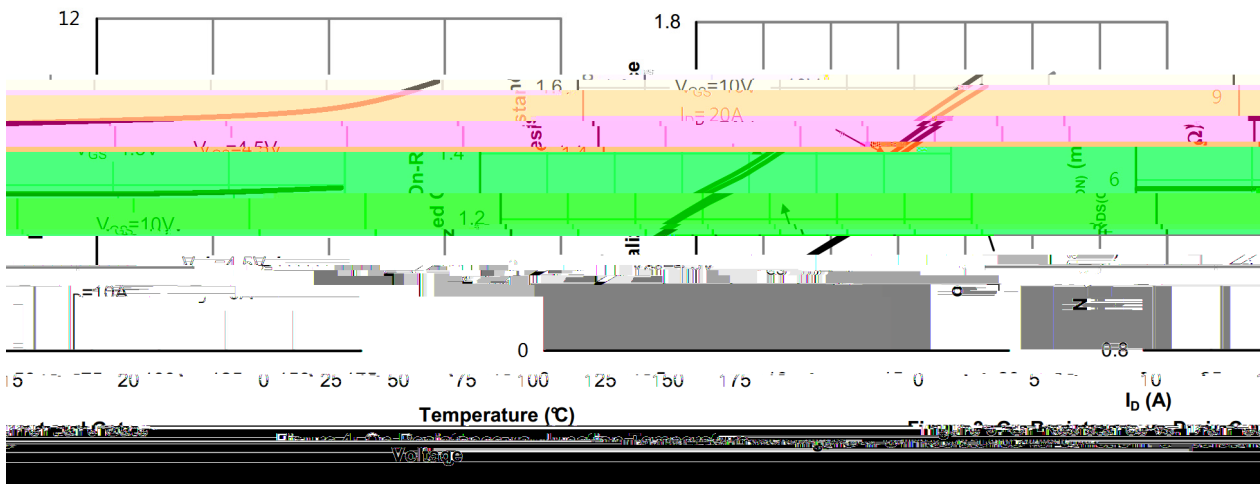
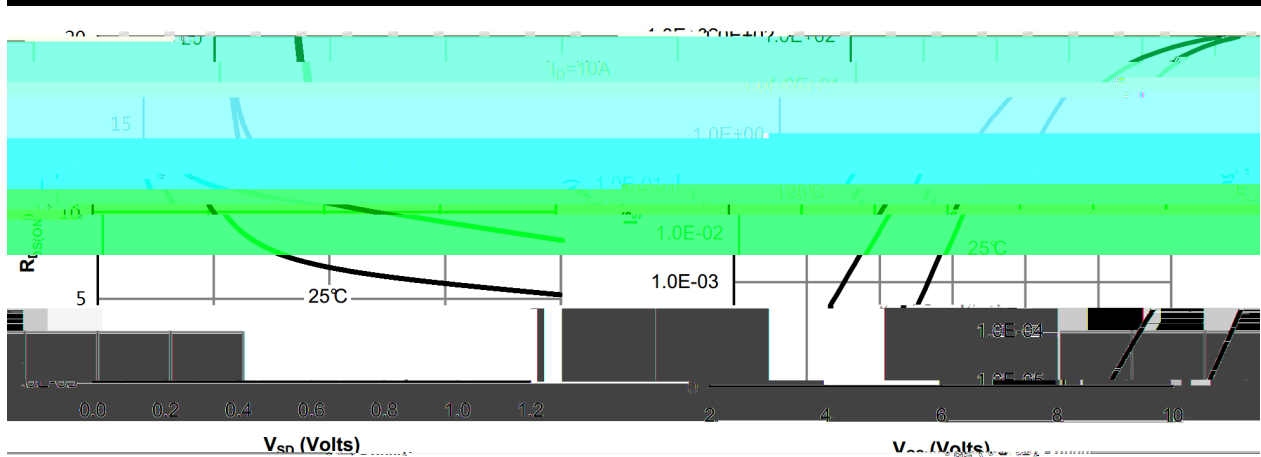
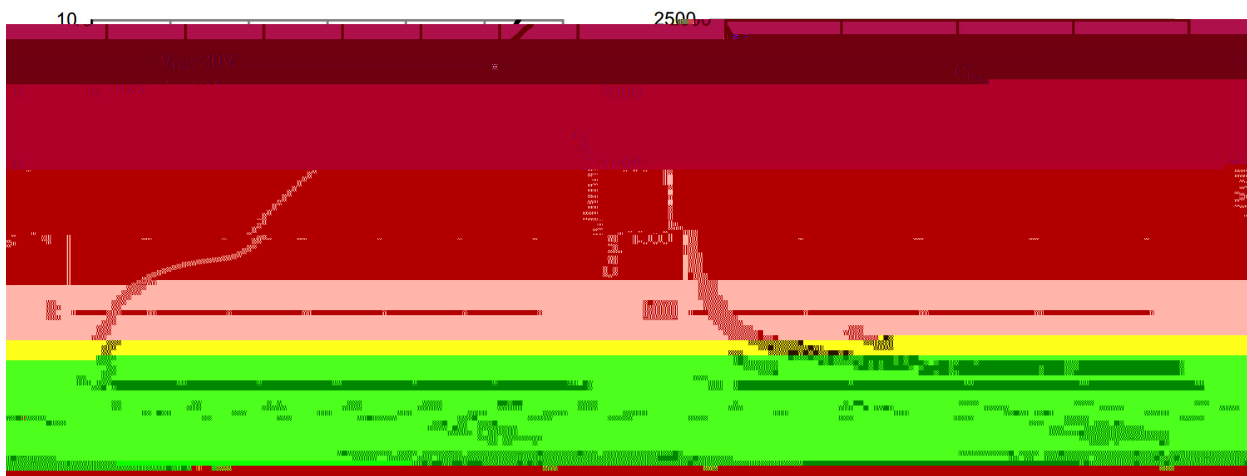
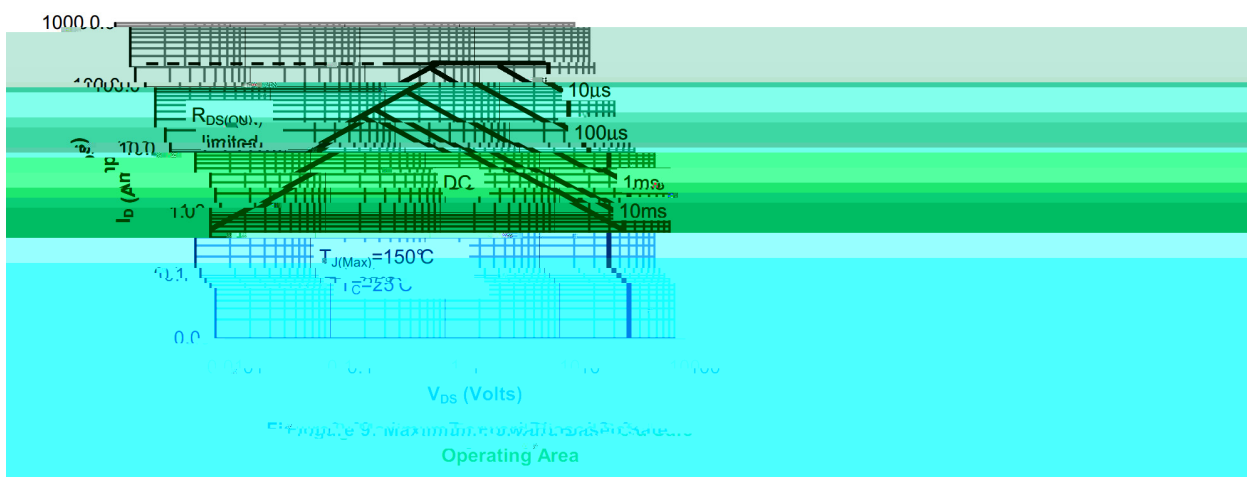
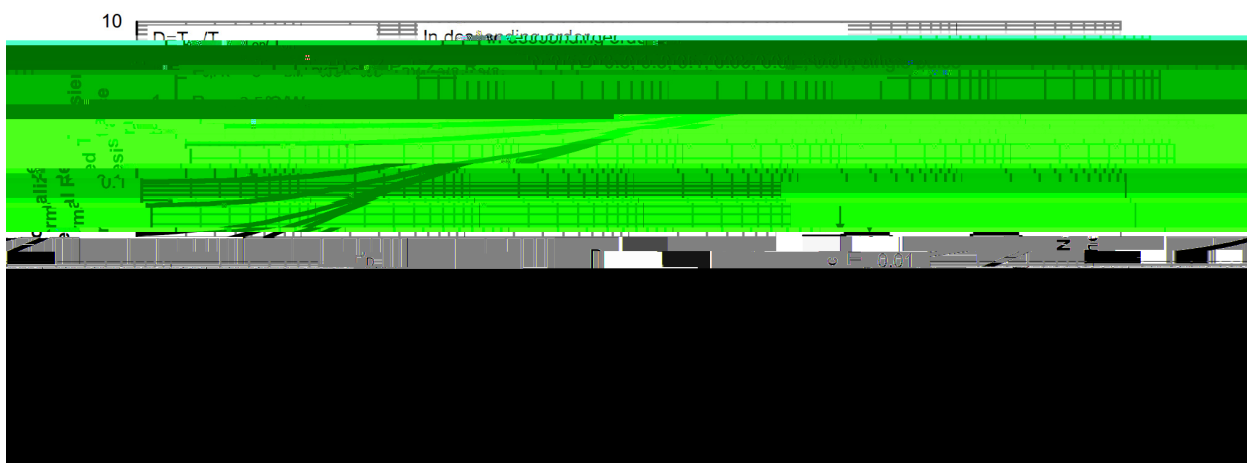


Figure 3: On-Resistance vs. Gate-Source Voltage

Figure 3: On-Resistance vs. Gate-Source Voltage

/ Electrical Characteristic Curve



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/ Marking Instructions

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() / Temperature Profile for IR Reflow Soldering(Pb-Free)